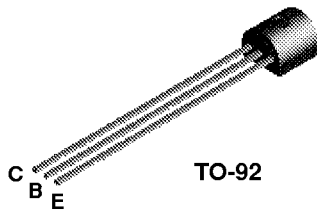
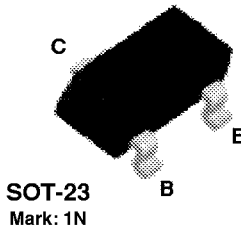


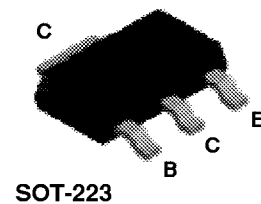
MPSA14



MMBTA14



PZTA14



NPN Darlington Transistor

This device is designed for applications requiring extremely high current gain at collector currents to 1.0 A. Sourced from Process 05.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	30	V
V_{CBO}	Collector-Base Voltage	30	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current - Continuous	1.2	A
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max			Units
		MPSA14	*MMBTA14	**PZTA14	
P_D	Total Device Dissipation	625	350	1,000	mW
	Derate above 25°C	5.0	2.8	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

* Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

** Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

NPN Darlington Transistor

(continued)

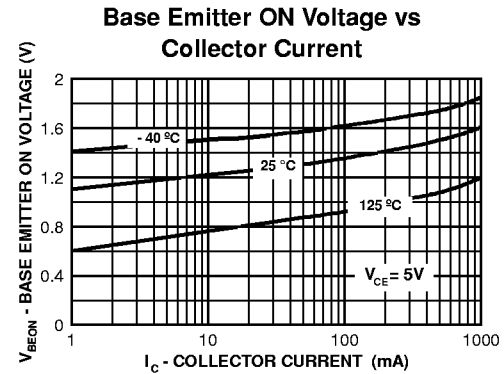
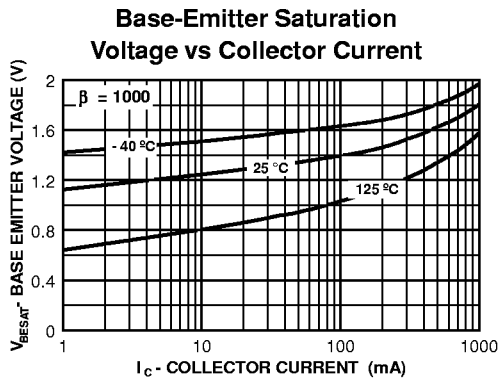
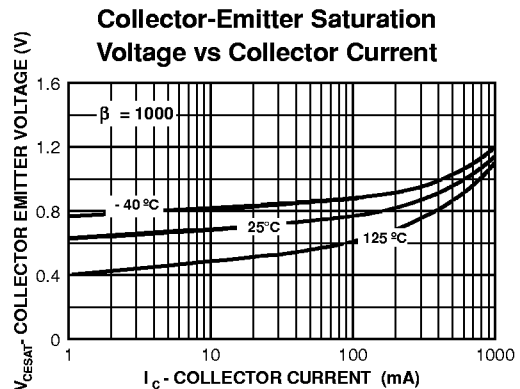
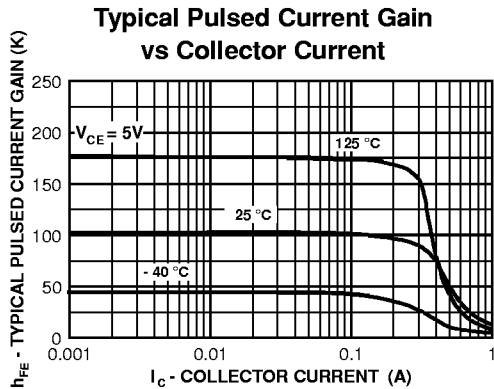
Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$I_C = 100 \mu A, I_B = 0$	30		V
I_{CBO}	Collector-Cutoff Current	$V_{CB} = 30 V, I_E = 0$		100	nA
I_{EBO}	Emitter-Cutoff Current	$V_{EB} = 10 V, I_C = 0$		100	nA
ON CHARACTERISTICS*					
h_{FE}	DC Current Gain	$I_C = 10 mA, V_{CE} = 5.0 V$ $I_C = 100 mA, V_{CE} = 5.0 V$	10,000 20,000		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 100 mA, I_B = 0.1 mA$		1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 100 mA, V_{CE} = 5.0 V$		2.0	V
SMALL SIGNAL CHARACTERISTICS					
f_T	Current Gain - Bandwidth Product	$I_C = 10 mA, V_{CE} = 5 V,$ $f = 100 MHz$	125		MHz

*Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2.0\%$

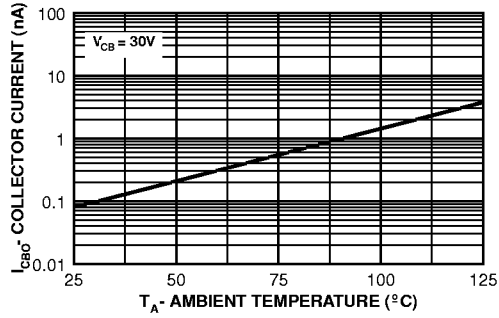
Typical Characteristics



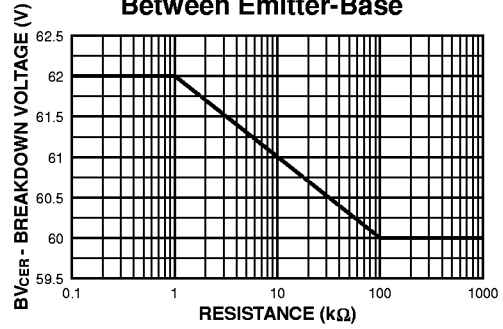
NPN Darlington Transistor
(continued)

Typical Characteristics (continued)

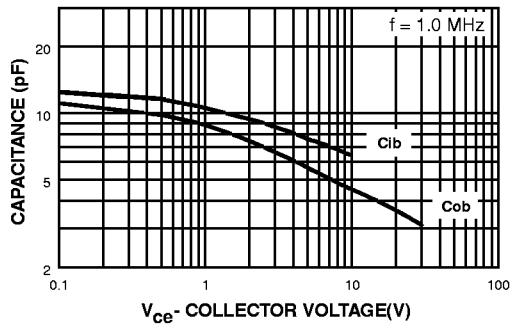
Collector-Cutoff Current vs Ambient Temperature



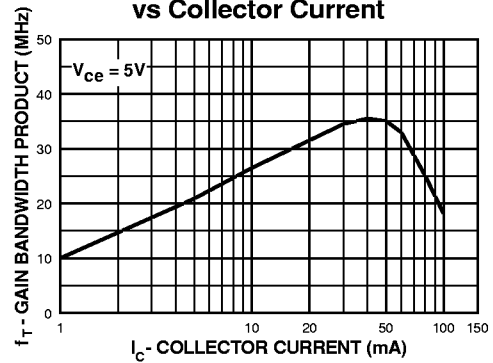
Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base



Input and Output Capacitance vs Reverse Voltage



Gain Bandwidth Product vs Collector Current



Power Dissipation vs Ambient Temperature

